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Sheet 1 of 5

Form PTO-1448 <b>LIST OF ART CITED BY APPLICANT</b> <small>(Use several sheets if necessary)</small>				ATTY DOCKE L.O. MI22-1398	SERIAL NO. 09/536,037		
<b>#13</b> <small>SEP 04 2001</small>				APPLICANT Weimin (Michael) Li et al.			
				FILING DATE March 27, 2000	GROUP 2822		
<b>U.S. PATENT DOCUMENTS</b>							
Examiner	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
TMT	AA 4,474,975	10-2-1984	Clemans et al.	556	410	/	
	AB 5,952,581	10-5-1999	Hayase et al.	524	588	/	
	AC 4,805,883	2-21-1989	Magdo et al.	316	40	/	
	AD 5,874,367	2-23-1999	Dobson	438	787	/	
	AE 5,858,880	1-12-1999	Dobson et al.	438	758	/	
	AF 5,219,813	6-15-1993	Fabry et al.	438	758	/	
	AG 5,270,267	12-14-1993	Quillet	438	597	/	
	AH 5,541,445	7-30-1996	Quillet	438	761	/	
	AI 6,022,404	2-8-2000	Ettinger et al.	106	404	/	
	AJ 5,709,741	1-20-1998	Akamatsu et al.	106	387,11	/	
	AK 4,648,904	3-10-1987	DePasquale et al.	106	2	/	
	AL 4,158,717	6-19-1979	Nelson	428	446	/	
	AM 5,667,015	9-16-1997	Harestad et al.	166	383	/	
	AN 5,661,093	8-28-1997	Ravi et al.	438	763	/	
	AO 5,536,857	7-16-1996	Nerula et al.	556	10	/	
	AP 4,695,859	9-22-1987	Guba et al.	257	64	/	
	AQ 5,061,509	10-29-1991	Naito et al.	427	497	/	
	AR 4,800,671	7-15-1986	Saitoh et al.	430	57.5	/	
	AS 5,753,320	5-19-1998	Mikoshiba et al.	427	570	/	
	AT 5,358,515	10-16-1994	Tahara et al.	438	715	/	
	AU 4,954,867	9-4-1990	Hosaka	257	639	/	
	AV 5,674,358	10-7-1997	Nagayama	438	694	/	
	AW 5,731,242	3-24-1998	Parat et al.	438	586	/	
TMT	AX 5,741,721	4-21-1998	Stevens	438	396	/	
EXAMINER				DATE CONSIDERED			
T. M. Thomas				12-07-01			
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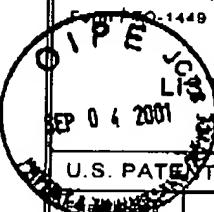
Form PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE <b>LIST OF ART CITED BY APPLICANT</b> (Use several sheets if necessary)					#13	ATTY. DOCKL #O M122-1398	SERIAL NO. 09/536,037
					APPLICANT Weimin (Michael) Li et al		
					FILING DATE March 27, 2000	GROUP 2822	
<b>U.S. PATENT DOCUMENTS</b>							
Examiner		Document Number	Date	Name		Class	Subclass
TMT	AA	5,034,348	7-23-1991	Harlewick et al.		438	453
	AB	5,472,827	12-5-1995	Ogawa et al.		430	315
	AC	5,472,828	12-5-1995	Ogawa		430	325
	AD	5,641,607	6-24-1997	Ogawa et al.		430	372,1
	AE	5,648,202	7-15-1997	Ogawa et al.		430	325
	AF	5,871,297	9-23-1997	Ogawa et al.  Koppe et al.		382	293
	AG	5,877,111	10-14-1997	Ogawa		430	313
	AH	5,898,352	12-16-1997	Ogawa et al.		430	14
	AI	5,831,321	11-3-1998	Nagayama		257	412
	AJ	5,591,566	1-7-1997	Ogawa		430	325
	AK	6,008,124	12-28-1999	Sakiguchi et al.		438	653
	AL	5,340,621	6-23-1994	Matsumoto et al.		427	571
	AM	5,600,185	2-4-1997	Tsukamoto et al.		257	323
	AN	5,872,385	2-16-1999	Taft et al.		257	437
	AO	5,960,289	9-28-1999	Tsui et al.		438	275
	AP	5,868,324	10-19-1998	Cheung et al		204	192,28
	AQ	6,020,243	2-1-2000	Wallace et al.		438	287
	AR	5,441,787	6-16-1995	Hogan et al.		428	209
	AS	5,710,067	1-20-1998	Fooja et al.		438	636
	AT	5,759,755	6-2-1998	Park et al.		430	512
	AU	5,838,052	11-17-1998	McTeer		257	437
	AV	5,883,011	3-16-1999	Lin et al.		438	747
	AW	6,140,151	10-31-2000	Akram		438	113
TMT	AX	5,314,724	5-24-1994	Tsukune et al.		427	489
EXAMINER					DATE CONSIDERED		
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 <b>U.S. DEPARTMENT OF COMMERCE</b> <b>PATENT AND TRADEMARK OFFICE</b> <b>LIST OF ART CITED BY APPLICANT</b> <small>(Use several sheets if necessary)</small>					ATTY. DOCK # O. MI22-1398	SERIAL NO. 09/536,037		
					APPLICANT Weimin (Michael) Li et al.			
# 13					FILING DATE March 27, 2000	GROUP 2822		
<b>U.S. PATENT DOCUMENTS</b>								
Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
TMT	AA	5,376,591	12-27-1994	Maeda et al.	438	761		
	AB	5,817,549	10-6-1998	Yemazaki et al.	438	166		
	AC	6,001,741	12-14-1999	Aliers	438	706		
	AD	6,072,227	6-6-2000	Yau et al.	357	642		
TMT	AE	6,788,039	7-20-1998	Brouquet	407	578		
	AF							
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	AX							
EXAMINER					DATE CONSIDERED			
T. M. Thomas					12-07-01			
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				APPLICANT Weimin (Michael) Li et al.			
				FILING DATE March 27, 2000	GROUP 2822		
<b>FOREIGN PATENT DOCUMENTS</b>							
Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
TMT	AA	06067019A	9/1999	Japan (Glass)(Abstract)			
	AB	6-244172	9/1994	Japan			
	AC	593,727	10/1967	GB			
	AD	5-263255	10/1993	Japan			
	AE	0 471 185 A2	7/10/91	EPO			
	AF	0 588 087 A2	8/18/93	EPO			
	AG	0 588 087 A3	8/18/93	EPO			
	AH	09055351	23/2/97	Japan			
	AI	0 778 496 A2	05/12/96	EPO			
	AJ	20029	US99	Search Report			
	AK	20030	US99	Search Report			
TMT	AL	0 942330	9-99	EPO (Joubert)			
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	AR						
	AS						
	AT						
	AU						
	AW						
EXAMINER				DATE CONSIDERED			
T. M. Thomas				12-07-01			
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Form PTO-1449 <i>CIPS</i> <b>LIST OF ART CITED BY APPLICANT</b> (use several sheets if necessary) SEP 04 2001			#13	ATTY. DOCKE J.O. MI22-1388	SERIAL NO. 09/536,037
			APPLICANT Weimin (Michael) Li et al.		
			FILING DATE March 27, 2000	GROUP 2822	
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)					
Examiner's Initials		Name			
TMT	AA	TEXT: Jenkins, F. et al., "Fundamentals of Optics", Properties of Light, pp. 9-10. (No date)			
	AB	TEXT: Wong, S. et al., "Silicon Processing for the VLSI Era", Vol. 1, pp. 437-441. (No date)			
	AC	D.R. McKenzie et al., "New Technology for PACVO", Surface and Coatings Technology, 62 (1998), pp. 326-333.			
	AD	S. McClatchie et al., "Low Dielectric Constant Flowfill® Technology For IMD Applications"; undated; 7 pages			
	AE	K. Beekmann et al., "Sub-micron Gap Fill and In-Situ Planarisation using Flowfill™ Technology"; October 1995; pp. 1-7			
	AF	A. Kiermasz, et al., "Planarisation for Sub-Micron Devices Utilising a New Chemistry", Electrotech, February 1995; 2 pages			
	AG	IBM Technical Disclosure Bulletin "Low-Temperature Deposition of SiO <sub>2</sub> , Si <sub>3</sub> N <sub>4</sub> or SiO <sub>2</sub> -Si <sub>3</sub> N <sub>4</sub> ", Vol. 28, No. 9, p. 4170, Feb. 1986.			
	AH	ARTICLE: Benchar, C. et al., "Dielectric antireflective coatings for DUV lithography", Solid State Technology (March 1997), pp.109-114.			
	AI	Noboru Shibata, "Plasma-Chemical Vapor-Deposited Silicon Oxide/Silicon Oxynitride Double-Layer Antireflective Coating for Solar Cells", Japanese Journal of Applied Physics, Vol. 30, No. 5, May 1991, pp. 997-1001.			
	AJ	Ralls, Kenneth M., "Introduction to Materials Science and Engineering", John Wiley & Sons, © 1976, pp. 312-313			
	AK	Revi K. Laxman, "Synthesizing Low-k CVD Materials for Fab Use", Semiconductor International, Nov. 2000, 10 pps.			
	AL	Anonymous, "New gas helps make faster IC's", Machine Design Cleveland, © Penton Media, Inc., November 4, 1999, pp. 118			
	AM	Loboda et al., "Using Trimethylsilane to Improve Safety Throughput and Versatility in PECVD Processes", 4th International Symposium on Silicon Nitride and Silicon Dioxide Thin Insulating Films, The Electrochemical Society, Abstract No. 358, p. 454, May 1997.			
	AN	ARTICLE: Dammel, R. R. et al., "Dependence of Optical Constants of AZ® BARLI™ Bottom Coating on Back Conditions", SPIE Vol. 3049 (1997), pp. 963-973.			
	AO	TEXT: Heavens, O. S., "Optical Properties of Thin Solid Films", pp. 48-49.			
	AP	Wilkmann, R. et al., "Matrix Reactions of Methyisilanes and Oxygen Atoms", Phys. Chem 1988, pp. 594-602.			
	AQ	Weidman, T. et al., "New photodefinable glass etch masks for entirely dry photolithography: Plasma deposited organosilicon hydride polymers", Appl. Phys. Lett 1-25-93, pp. 372-374.			
	AR	Weidman, et al., "All Dry Lithography: Applications of Plasma Polymerized Methylsilane as a Single Layer Resist and Silicon Dioxide Precursor", Journal of Photopolymer Science and Technology, V. 8, #4, 1995, pp. 679-686.			
	AS	Joubert et al., "Application of Plasma Polymerized Methylsilane in an all dry resist process for 193 and 248 nm Lithography", Microelectronic Engineering 30 (1996), pp. 275-278.			
	AT	Joshi, A.M. et al., "Plasma Deposited Organosilicon Hydrido Network Polymers as Versatile Resists for Entirely Dry Mid-Deep UV Photolithography", SPIE Vol. 1925, pp. 709-720.			
	AU	Matsuura, M. et al., "Highly Reliable Self-Planarizing Low-k Intermetal Dielectric for Sub-quarter Micron Interconnects", IEEE 1997, pp. 785-788.			
TMT	AV	Horie, O. et al., "Kinetics and Mechanism of the Reactions of ...", J. Phys. Chem 1991, 1393-400.			
EXAMINER		DATE CONSIDERED			
<i>T. M. Thomas</i>			12-07-01		
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